AMENDMENTS TO THE CLAIMS

Please enter the following amendments:

1 – 26. (Canceled)

27. (Currently Amended) A ridge stripe semiconductor laser device comprising an active layer, upper and lower clad layers that sandwich the active layer therebetween, a stripe-shaped ridge formed in part of the upper clad layer, and a current block layer that covers both sides of the stripe-shaped ridge other than a top face thereof,

wherein a first electrode is formed on an upper face of the semiconductor laser device, and a second electrode is formed on the first electrode,

wherein the first electrode is made thinner than the second electrode, and is so formed as to extend to both stripe-direction ends of the ridge while covering at least an entire area of the top face thereof, and

wherein the second electrode is formed ~~at a given distance~~ away from both stripe-direction ends of the ridge and ~~at a given distance~~ away from both width-direction ends, the width-direction intersecting the stripe-direction of the ridge.

28. (Currently Amended) A multibeam semiconductor laser device comprising, on a common semiconductor substrate, a plurality of ridge stripe semiconductor laser portions, each comprising an active layer, upper and lower clad layers that sandwich the active layer therebetween, a stripe-shaped ridge formed in part of the upper clad layer, and a current block layer that covers both sides of the stripe-shaped ridge other than a top face thereof,

wherein a first electrode is formed on an upper face of each of the semiconductor laser portions, and a second electrode is formed on the first electrode,

wherein the first electrode is made thinner than the second electrode, and is so formed as to extend to both stripe-direction ends of the ridge while covering at least an entire area of the top face thereof, and

wherein the second electrode is formed ~~at a given distance~~ away from both stripe-direction ends of the ridge and ~~at a given distance~~ away from both width-direction ends, the width-direction intersecting the stripe-direction of the ridge.

29. (Previously Presented) The semiconductor laser device according to claim 27,

wherein a width direction length of the first electrode is shorter than a width-direction length of the second electrode.

30. (Previously Presented) The semiconductor laser device according to claim 28,

wherein a width direction length of the first electrode is shorter than a width-direction length of the second electrode.

31. (Previously Presented) The semiconductor laser device according to claim 28,

wherein, between the plurality of semiconductor laser portions, a groove for electrically separating the semiconductor laser portions from each other is formed, and

wherein the first electrode is formed away from the groove.

32. (Withdrawn) A method for fabricating a ridge stripe semiconductor laser device comprising an active layer, upper and lower clad layers that sandwich the active layer therebetween, a stripe-shaped ridge formed in part of the upper clad layer, and a current block layer that covers both sides of the stripe-shaped ridge other than a top face thereof, the method for fabricating a ridge stripe semiconductor laser device comprising:

a first electrode forming step of forming a first electrode in such a way that at least an entire area of the top face of the ridge is covered therewith;

a second electrode forming step of forming a second electrode on the first electrode; and

a cleaving step of cleaving a facet of the semiconductor laser device that intersects the stripe-shaped ridge at right angles,

wherein, in the first electrode forming step, the first electrode is made thinner than the second electrode, and

wherein, in the second electrode forming step, the second electrode is formed at a given distance away from both stripe-direction ends of the ridge.

33. (Withdrawn) A method for fabricating a multibeam semiconductor laser device, the multibeam semiconductor laser device comprising, on a common semiconductor substrate, a plurality of ridge stripe semiconductor laser portions, each comprising an active layer, upper and lower clad layers that sandwich the active layer therebetween, a stripe-shaped ridge formed in part of the upper clad layer, and a current block layer that covers both sides of the stripe-shaped ridge other than a top face thereof, the method for fabricating a multibeam semiconductor laser device comprising:

a first electrode forming step of forming a first electrode in such a way that at least an entire area of the top face of each ridge is covered therewith;

a second electrode forming step of forming a second electrode on the first electrode; and

a cleaving step of cleaving a facet of the semiconductor laser device that intersects the stripe-shaped ridge at right angles,

wherein, in the first electrode forming step, the first electrode is made thinner than the second electrode, and

wherein, in the second electrode forming step, the second electrode is formed at a given distance away from both stripe-direction ends of the ridge.

34. (Withdrawn) The method for fabricating a semiconductor laser device according to claim 32,

wherein, by the second electrode forming step, a width direction length of the second electrode is made longer than a width direction length of the first electrode.

35. (Withdrawn) The method for fabricating a semiconductor laser device according to claim 33,

wherein, by the second electrode forming step, a width direction length of the second electrode is made longer than a width direction length of the first electrode.

36. (Previously Presented) The method for fabricating a semiconductor laser device according to claim 33, further comprising:

a groove forming step of forming a groove between the plurality of semiconductor laser portions for electrically separating the semiconductor laser portions from each other,

wherein, in the first electrode forming step, the first electrode is formed away from the groove.

37. (Withdrawn) The method for fabricating a semiconductor laser device according to claim 32,

wherein at least one of the first electrode forming step and the second electrode forming step uses lift-off for electrode formation.

38. (Withdrawn) The method for fabricating a semiconductor laser device according to claim 33,

wherein crystal growth including first crystal growth and second crystal growth is performed on the semiconductor substrate for forming a first semiconductor laser portion,

wherein, after a crystal grown by the first and second crystal growth in another region other than where the first semiconductor laser portion is left is removed, crystal growth is

performed on the semiconductor substrate for forming a second semiconductor laser in the another region on the semiconductor substrate,

when the crystal grown by the first and second crystal growth in the another region is removed, the method for fabricating a semiconductor laser device further comprising:

a second crystal growth layer removing step of removing the crystal grown by the second crystal growth in such a way that a layer of the crystal grown by the first crystal growth is exposed; and

a first crystal growth layer removing step of removing the crystal grown by the first crystal growth.

39. (Withdrawn) The method for fabricating a semiconductor laser device according to claim 38,

wherein a growth temperature at a time of the second crystal growth is so set as to be lower than a growth temperature at a time of the first crystal growth.

40. (Previously Presented) The semiconductor laser device according to claim 27, wherein a film thickness of the first electrode is equal to or smaller than 100 nm.

41. (Previously Presented) The semiconductor laser device according to claim 28, wherein a film thickness of the first electrode is equal to or smaller than 100 nm.